New Release

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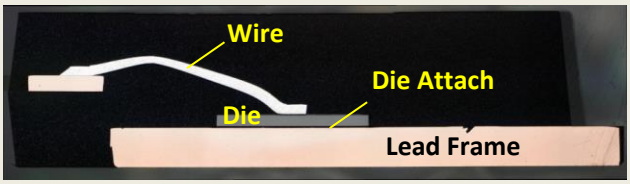
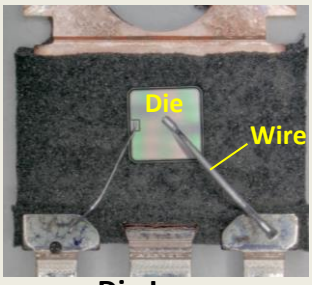
ST Micro electronics SCT30N120 SiC POWER PACKAGE ANALYSIS REPORT

July,5 2016. This is a detailed package analysis report of the SCT30N120 SiC Power device. This product realizes the continuous operation at 200℃.

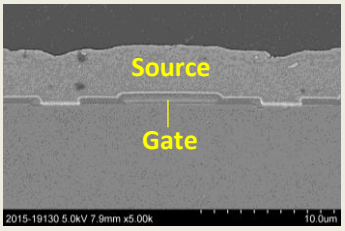
Package



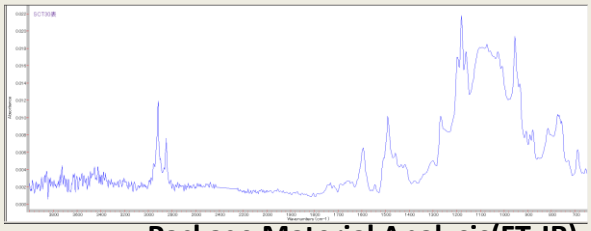
Package Cross section



Die Image



Die Cross section



Package Material Analysis(FT-IR)

The packaging technologies are key for realizing high temperature continuous operation. Packaging key technologies to realize 200℃ continuous operation are highlighted in this report by comparing 4 products as below . Detail analysis of surface treatment of power devices , die attachment, wire bonding and materials are conducted in 35 pages report.

- ✓ **SiC device : STMicro SCT30N120 (1200V) Tjmax=200℃**
- ✓ SiC device : ROHM SCH2080KE (1200V) Tjmax=175℃
- ✓ Silicon device: STMicro STGW40V60DLF (600V IGBT) Tjmax=175℃
- ✓ Silicon device : Infineon SPI21N10 (100V MOSFET) Tjmax=175℃

Priced to sell at $3,500

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